SN74HC266 Quadruple 2-Input XNOR Gates with Open-Drain Outputs

1 Features

- Wide Operating Voltage Range: 2 V to 6 V
- Outputs Can Drive Up To 10 LSTTL Loads
- Low Power Consumption, 20-µA Maximum I_{CC}
- Typical t_{pd} = 8 ns at 5 V
- ±4-mA Output Drive at 5 V
- Low Input Current of 1 µA

2 Applications

- Selectable buffer/inverter
- Clock phase difference detector

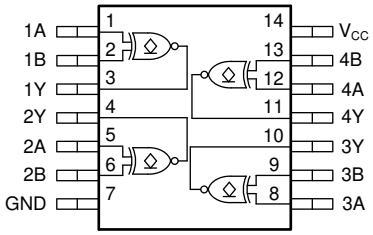
3 Description

This device contains four independent 2-input XNOR Gates with open-drain outputs. Each gate performs the Boolean function $Y = \overline{A \oplus B}$ in positive logic.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74HC266N	PDIP (14)	19.30 mm × 6.40 mm
SN74HC266NS	SO (14)	10.20 mm × 5.30 mm
SN74HC266D	SOIC (14)	8.70 mm × 3.90 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Functional pinout of the SN74HC266

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision F (August 2003) to Revision G (April 2021)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1
• Updated to new TIS format	1

5 Pin Configuration and Functions

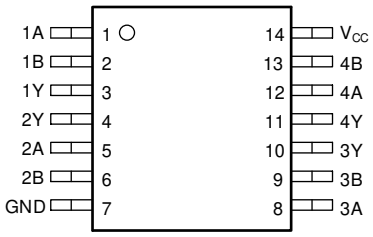


Figure 5-1. D, N, or NS Package
14-Pin SOIC, PDIP, or SO
Top View

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	1	Input	Channel 1, Input A
1B	2	Input	Channel 1, Input B
1Y	3	Output	Channel 1, Output Y
2Y	4	Output	Channel 2, Output Y
2A	5	Input	Channel 2, Input A
2B	6	Input	Channel 2, Input B
GND	7	—	Ground
3A	8	Input	Channel 3, Input A
3B	9	Input	Channel 3, Input B
3Y	10	Output	Channel 3, Output Y
4Y	11	Output	Channel 4, Output Y
4A	12	Input	Channel 4, Input A
4B	13	Input	Channel 4, Input B
V_{CC}	14	—	Positive Supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
I_{IK}	Input clamp current(2)	$V_I < 0$ or $V_I > V_{CC}$		±20	mA
I_{OK}	Output clamp current(2)	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_J	Junction temperature(3)			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) Guaranteed by design.

6.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2	5	6	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5			V
		V_{CC} = 4.5 V	3.15			
		V_{CC} = 6 V	4.2			
V_{IL}	Low-level input voltage	V_{CC} = 2 V			0.5	V
		V_{CC} = 4.5 V			1.35	
		V_{CC} = 6 V			1.8	
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
t_t	Input transition time	V_{CC} = 2 V			1000	ns
		V_{CC} = 4.5 V			500	
		V_{CC} = 6 V			400	
T_A	Operating free-air temperature		–40		85	°C

6.3 Thermal Information

THERMAL METRIC(1)		SN74HC266			UNIT
		N (PDIP)	D (SOIC)	NS (SOP)	
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	62.5	133.6	122.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	42.4	89.0	81.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	50.2	89.5	83.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	29.8	45.5	45.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	42.0	89.1	83.4	°C/W

THERMAL METRIC(1)		SN74HC266			UNIT
		N (PDIP)	D (SOIC)	NS (SOP)	
		14 PINS	14 PINS	14 PINS	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.4 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			-40°C to 85°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
I_{OH}	High-level output current	V_I = V_{IH} or V_{IL}	V_O = V_{CC}	6 V		0.01	0.5			5	µA
V_{OL}	Low-level output voltage	V_I = V_{IH} or V_{IL}	I_{OL} = 20 µA	2 V		0.002	0.1			0.1	V
				4.5 V		0.001	0.1			0.1	
				6 V		0.001	0.1			0.1	
			I_{OL} = 4 mA	4.5 V		0.17	0.26			0.33	
			I_{OL} = 5.2 mA	6 V		0.15	0.26			0.33	
I_I	Input leakage current	V_I = V_{CC} or 0		6 V		±0.1	±100			±1000	nA
I_{CC}	Supply current	V_I = V_{CC} or 0	V_I = V_{CC} or 0	6 V			2			20	µA
C_i	Input capacitance			2 V to 6 V		3	10			10	pF

6.5 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM	TO	V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			–40°C to 85°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	Propagation delay (Low to High)	A or B	Y	2 V		60	125			155	ns
				4.5 V		13	25			31	
				6 V		10	23			26	
t_{PHL}	Propagation delay (High to Low)	A or B	Y	2 V		60	100			125	ns
				4.5 V		13	20			25	
				6 V		10	17			21	
t_t	Transition-time		Y	2 V		28	75			95	ns
				4.5 V		8	15			19	
				6 V		6	13			16	

6.6 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
C_{pd}	Power dissipation capacitance per gate	No load	2 V to 6 V		35		pF

6.7 Typical Characteristics

T_A = 25°C

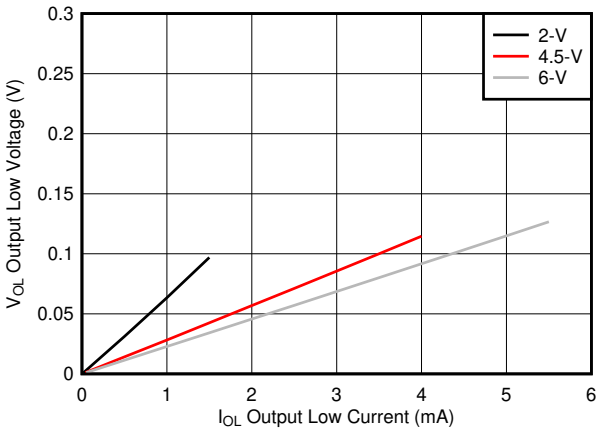
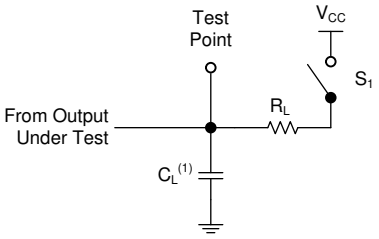


Figure 6-1. Typical output voltage in the low state (V_{OL})

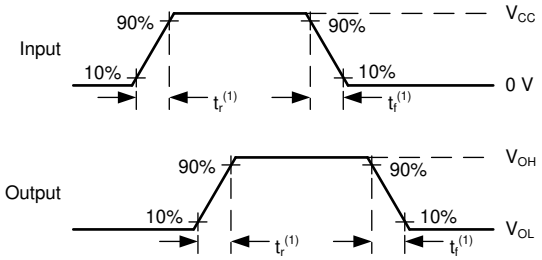
7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 6 ns.
- The outputs are measured one at a time, with one input transition per measurement.



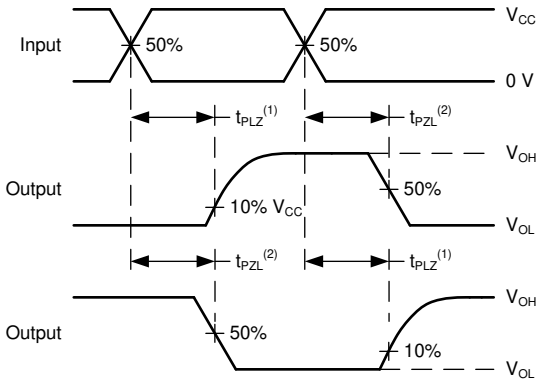
A. C_L= 50 pF and includes probe and jig capacitance.

Figure 7-1. Load Circuit



A. t_t is the greater of t_r and t_f.

Figure 7-2. Voltage Waveforms Transition Times



A. The maximum between t_{PLH} and t_{PHL} is used for t_{pd}.

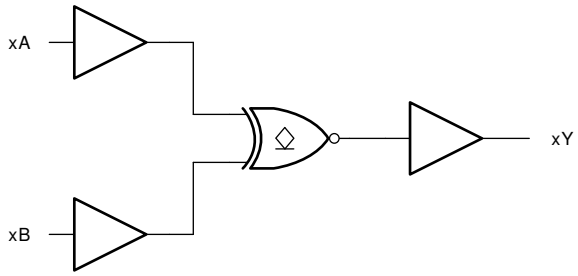
Figure 7-3. Voltage Waveforms Propagation Delays

8 Detailed Description

8.1 Overview

This device contains four independent 2-input XNOR gates with open-drain outputs. Each gate performs the Boolean function $Y = \overline{A \oplus B}$ in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 CMOS Open-Drain Outputs

The open-drain output allows the device to sink current to GND but not to source current from V_{CC}. When the output is not actively pulling the line low, it will go into a high impedance state. This allows the device to be used for a wide variety of applications, including up-translation and down-translation, as the output voltage can be determined by an external pull-up resistor.

The current drive capability of this device creates fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *Absolute Maximum Ratings*must be followed at all times.

The SN74HC266 can drive a load with a total capacitance less than or equal to the maximum load listed in the *Switching Characteristics* connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the *Absolute Maximum Ratings*.

8.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law (R = V ÷ I).

Signals applied to the inputs need to have fast edge rates, as defined by the input transition time in the *Recommended Operating Conditions* to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Figure 8-1.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

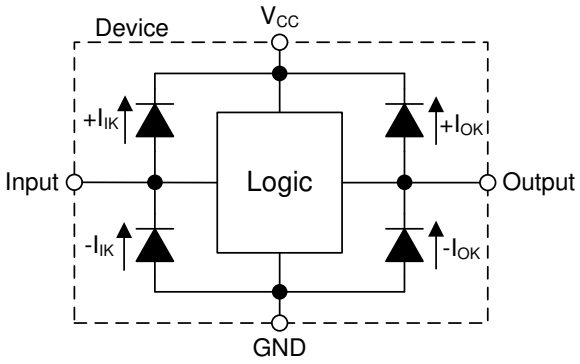


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 8-1. Function Table

INPUTS		OUTPUT
A	B	Y
L	L	Z
L	H	L
H	L	L
H	H	Z

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, one 2-input open-drain XNOR gate is used to create a selectable buffer or inverter as shown in *Figure 9-1*. This application allows for using a quad XNOR gate to produce any compbination of one to four buffers and inverters. Commonly each channel is permanently connected as either an inverter or buffer, however some systems do require the ability to switch between the two. If some channels are unused, the inputs can be grounded and the outputs left open.

9.2 Typical Application

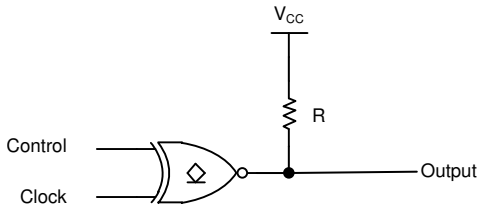


Figure 9-1. Typical application schematic

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HC266 plus the maximum supply current, I_{CC}, listed in *Electrical Characteristics*. The logic device can only sink as much current as is provided by the external pull-up resistor or other supply source. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, T_J(max) listed in the *Absolute Maximum Ratings*, is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HC266, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-kΩ resistor value is often used due to these factors.

The SN74HC266 has standard CMOS inputs, so input signal edge rates cannot be slow. Slow input edge rates can cause oscillations and damaging shoot-through current. The recommended rates are defined in the *Recommended Operating Conditions*.

Refer to *Section 8.3* for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*. The plot in the *Typical Characteristics* provides a typical relationship between output voltage and current for this device.

Open-drain outputs can be directly connected together to produce a wired-AND. This is possible because the outputs cannot source current, and thus can never be in bus-contention.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Section 8.3* for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in *Section 11*.
2. Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HC266 to the receiving device.
3. Ensure the resistive load at the output is larger than (V_{CC} / I_O(max)) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

9.2.3 Application Curves

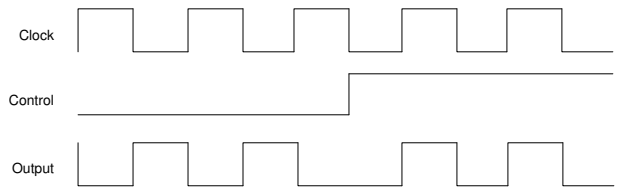


Figure 9-2. Typical application timing diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Figure 11-1*.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

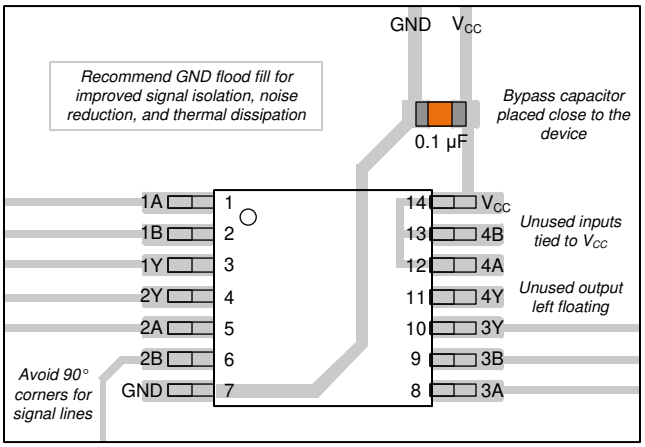


Figure 11-1. Example layout for the SN74HC266

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- Designing with Logic

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

12.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HC266D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC266	Samples
SN74HC266DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	HC266	Samples
SN74HC266DT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC266	Samples
SN74HC266N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC266N	Samples
SN74HC266NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC266	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

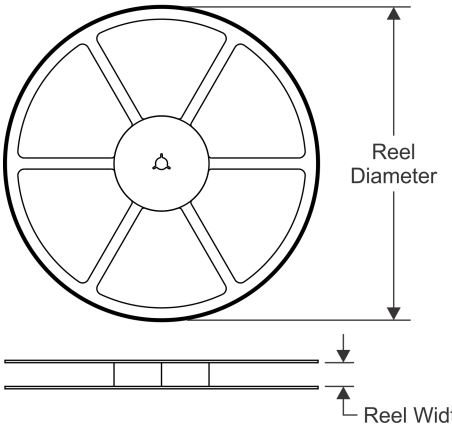
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

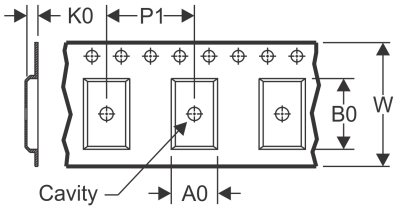
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

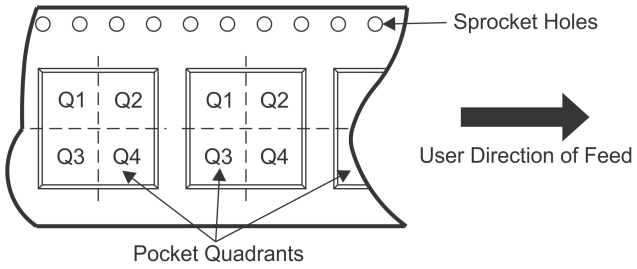


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

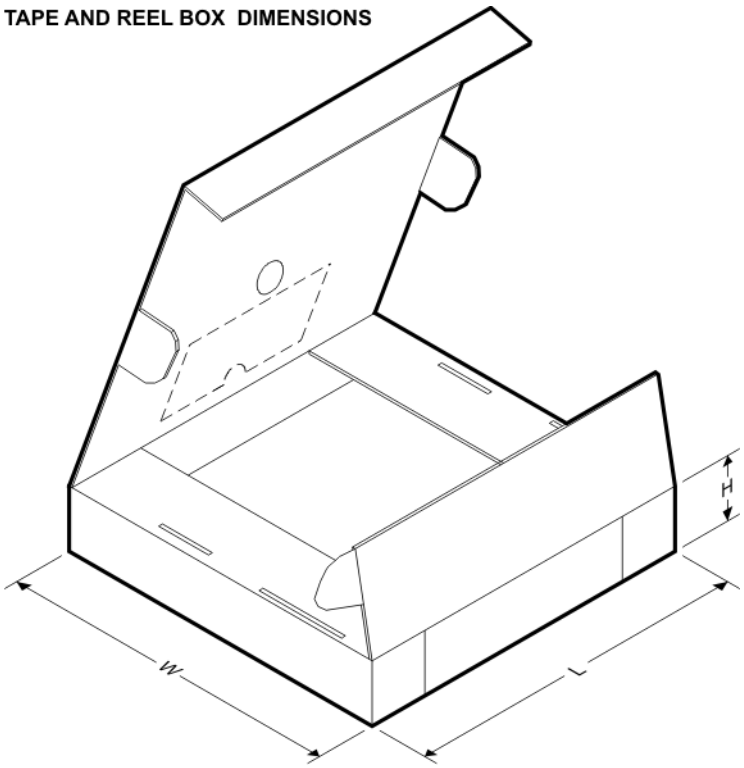
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC266DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC266DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HC266DT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC266NSR	SO	NS	14	2000	330.0	16.4	8.45	10.55	2.5	12.0	16.2	Q1

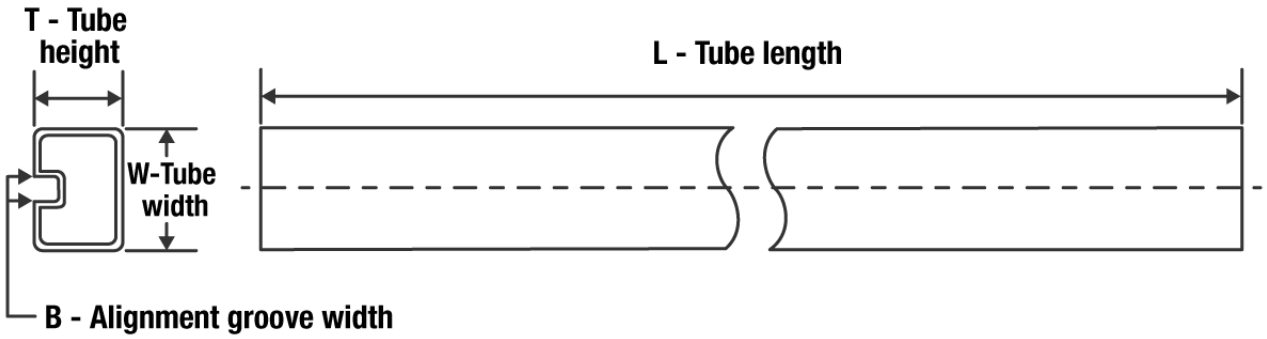
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC266DR	SOIC	D	14	2500	853.0	449.0	35.0
SN74HC266DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HC266DT	SOIC	D	14	250	210.0	185.0	35.0
SN74HC266NSR	SO	NS	14	2000	853.0	449.0	35.0

TUBE



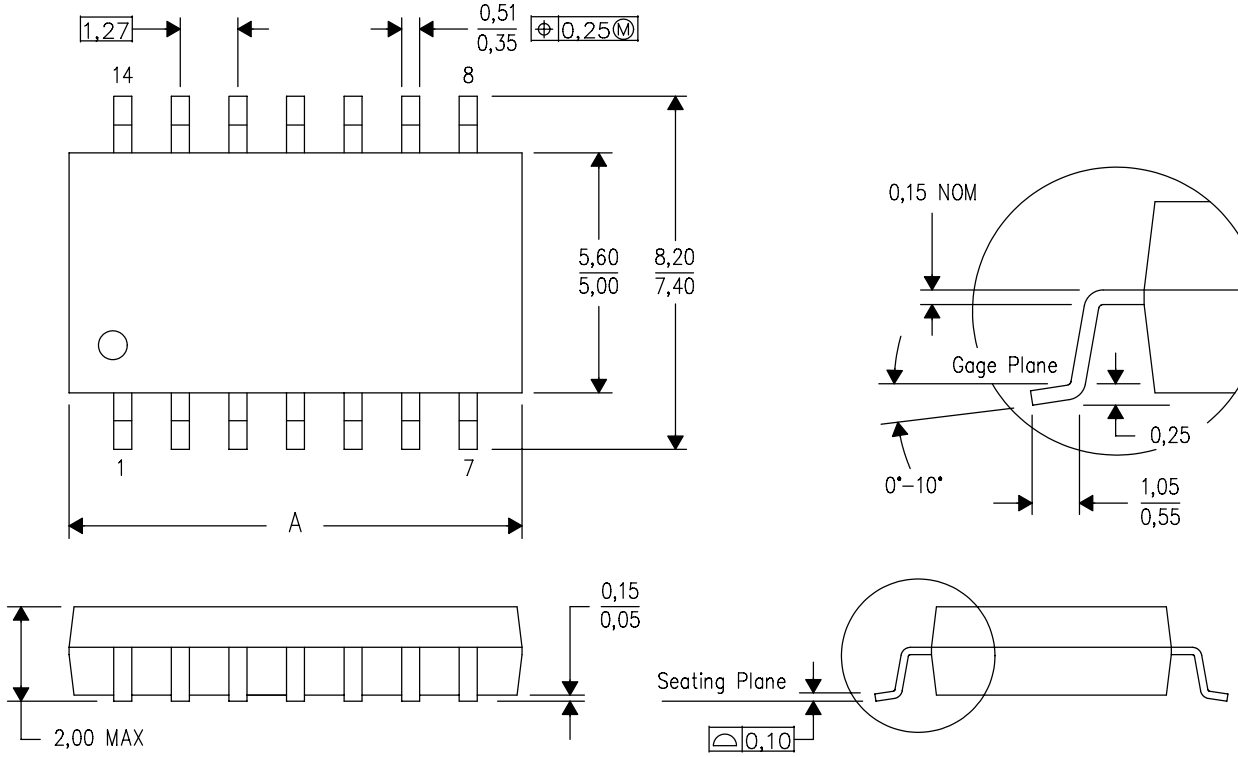
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74HC266D	D	SOIC	14	50	506.6	8	3940	4.32
SN74HC266N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC266N	N	PDIP	14	25	506	13.97	11230	4.32

MECHANICAL DATA

NS (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14-PINS SHOWN

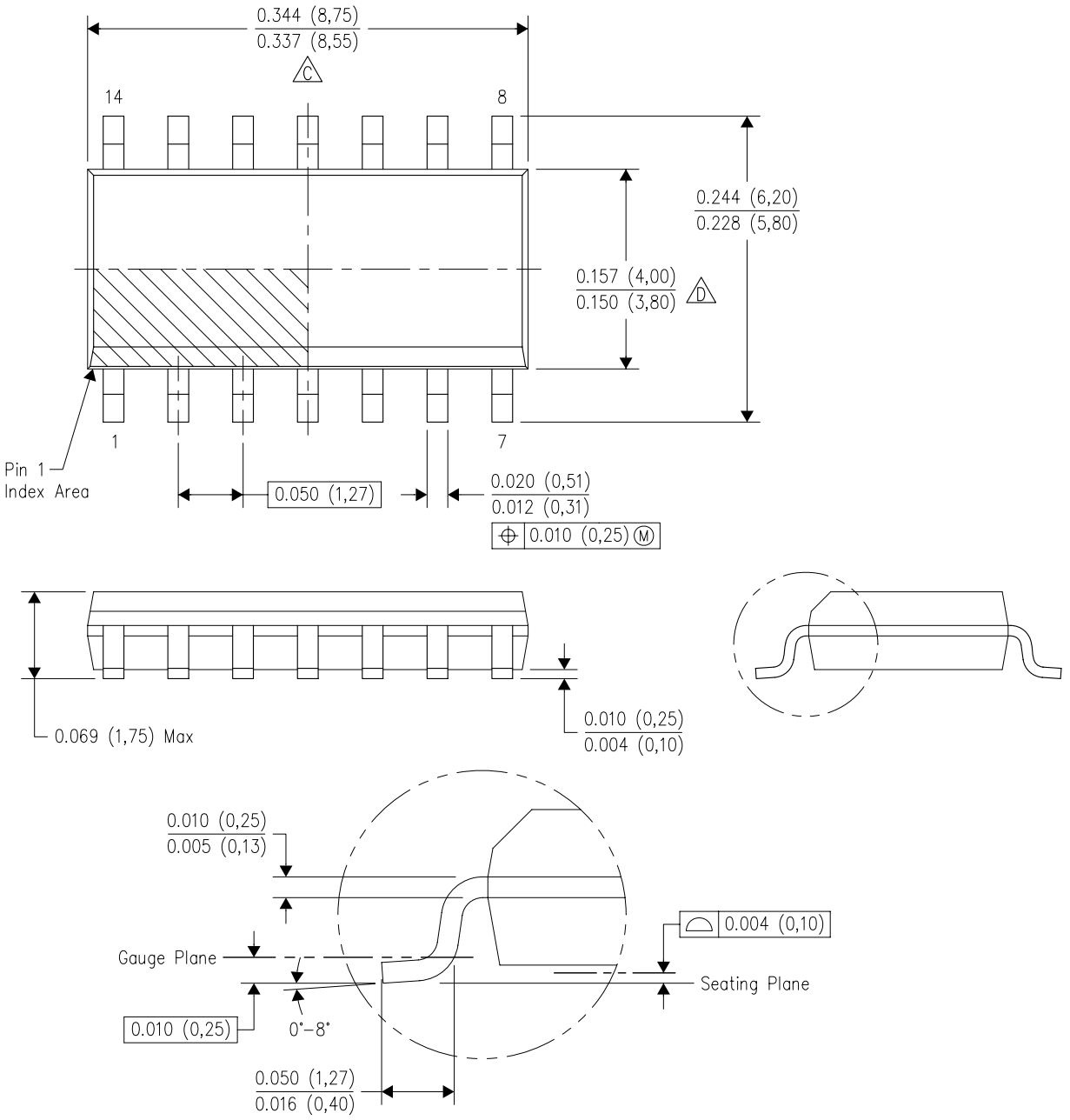


DIM \ PINS **	14	16	20	24
A MAX	10,50	10,50	12,90	15,30
A MIN	9,90	9,90	12,30	14,70

4040062/C 03/03

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

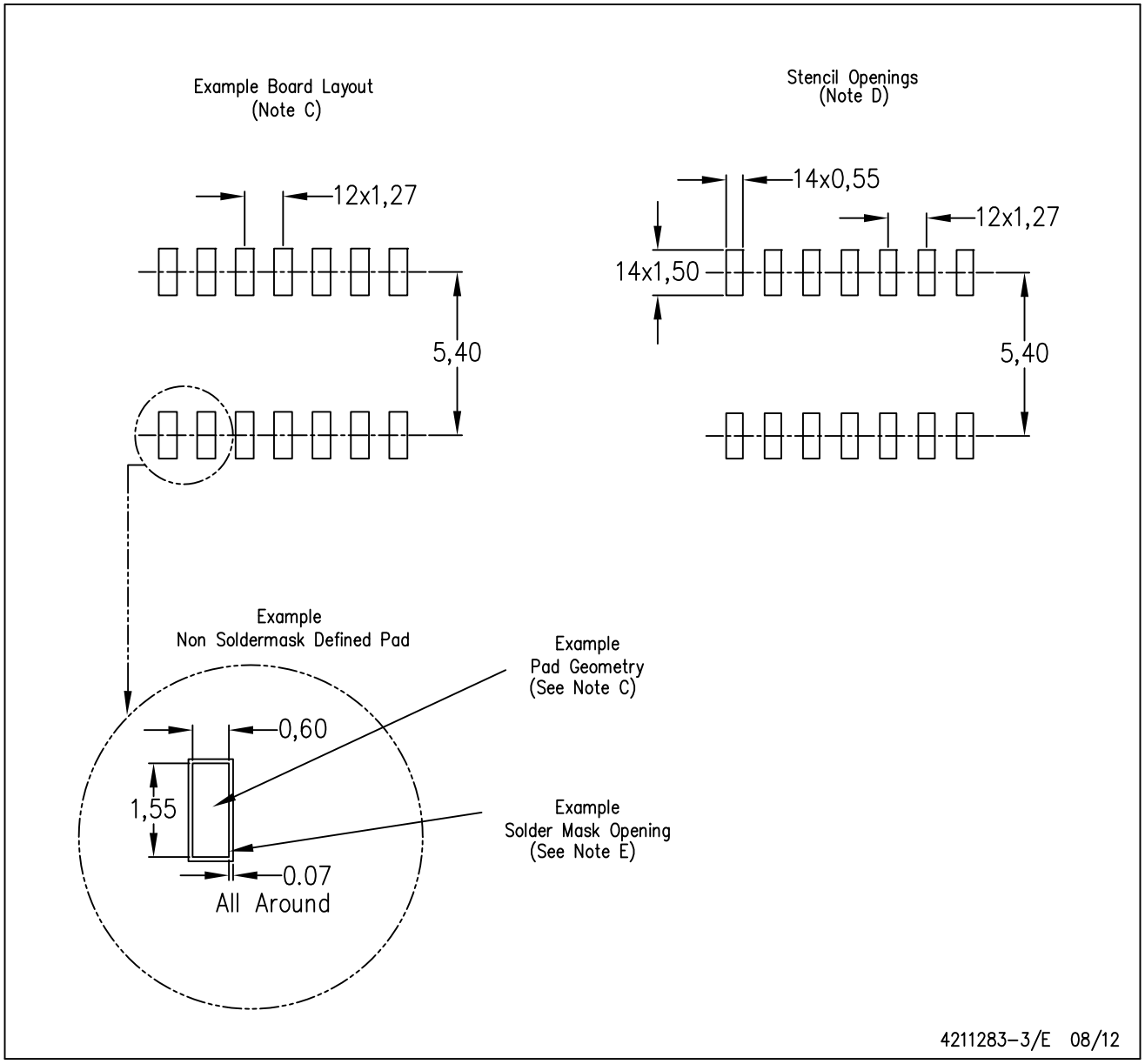
D (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040047–5/M 06/11

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AB.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE

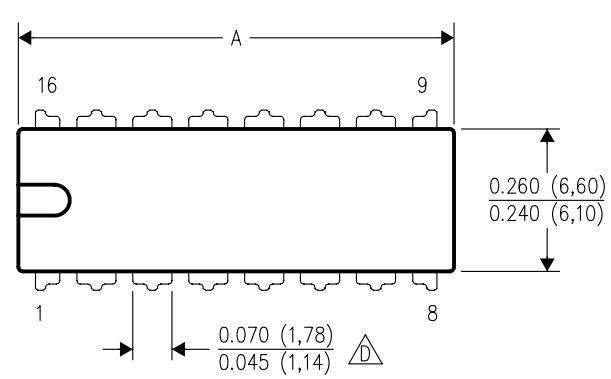


NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

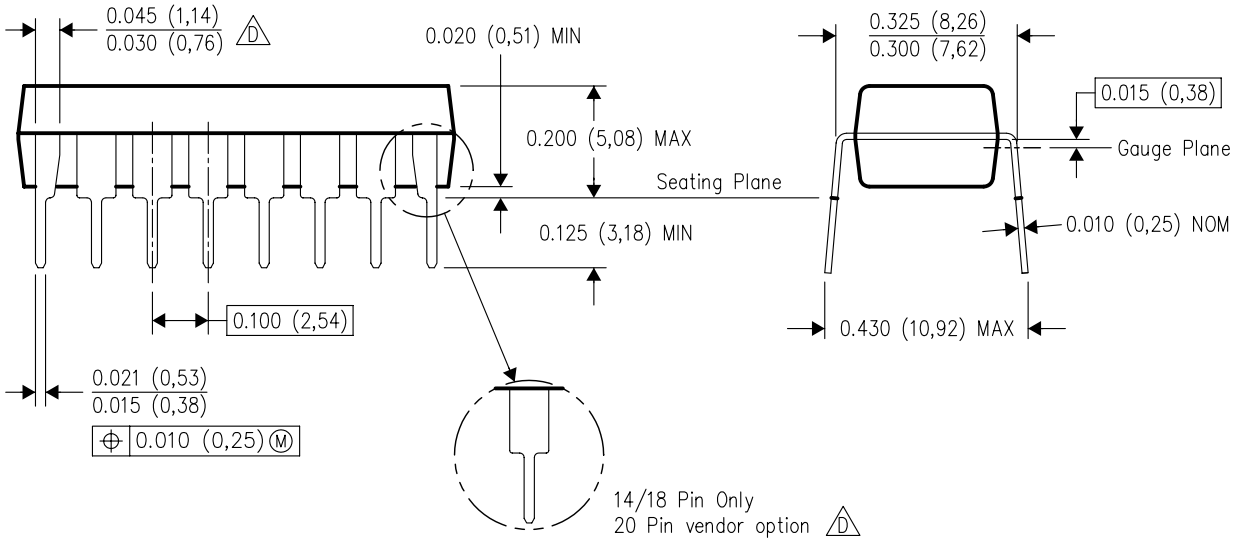
N (R–PDIP–T**)

PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN



DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



4040049/E 12/2002

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

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